



DESCRIPTION

These miniature surface mount MOSFETs reduce power loss conserve energy, making this device ideal for use in small power management circuitry. Typical applications are dc-dc converters, load switching, power management in portable and battery-powered products such as computers, printers, cellular and cordless telephones.

The BSS84L is available in SOT-23 Package

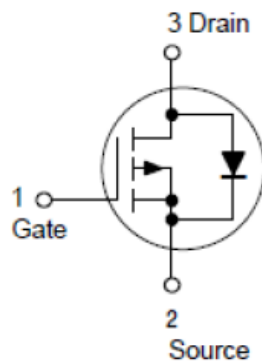
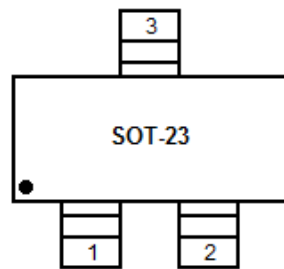
ORDERING INFORMATION

| Package Type | Part Number |
|--|--------------------|
| SOT-23 | BSS84L |
| Note | SPQ: 3,000pcs/Reel |
| AiT provides all RoHS Compliant Products | |

FEATURES

- Energy Efficient
- Available in SOT-23 Package

PIN DESCRIPTION





ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$

| | |
|---|--|
| V_{DSS} , Drain-to-Source Voltage | 50Vdc |
| V_{GS} , Gate-to-Source Voltage-Continuous | $\pm 20\text{Vdc}$ |
| I_D , Drain Current-Continuous @ $T_A = 25^\circ\text{C}$ | 130mA |
| I_{DM} , Pulsed Drain Current ($t_p \leq 10\mu\text{s}$) | 520mA |
| P_D , Total Power Dissipation @ $T_A = 25^\circ\text{C}$ | 225mW |
| T_J, T_{STG} , Junction and Storage temperature | $-55^\circ\text{C} \sim 150^\circ\text{C}$ |
| $R_{\theta JA}$, Thermal Resistance – Junction-to-Ambient | 556°C/W |
| T_L , Maximum Lead Temperature for Soldering Purposes, for 10 seconds | 260°C |

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



ELECTRICAL CHARACTERISTICS

T_A = 25°C

| Parameter | Symbol | Conditions | Min. | Typ. | Max. | Unit |
|--|----------------------|---|------|------|-----------------|------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-to-Source Breakdown Voltage | V _{(BR)DSS} | V _{GS} =0Vdc, I _D =250μAdc | 50 | - | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =25Vdc, V _{GS} =0Vdc V _{DS} =50Vdc, V _{GS} =0Vdc V _{DS} =50Vdc, V _{GS} =0Vdc, T _J =125°C | - | - | 0.1 15 60 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20Vdc, V _{DS} =0Vdc | - | - | ±10 | nA |
| ON CHARACTERISTICS^{NOTE1} | | | | | | |
| Gate-Source Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =250μAdc | 0.8 | - | 2.0 | V |
| Static Drain-to-Source On-Resistance | R _{DS(on)} | V _{GS} =5.0Vdc, I _D =100mAdc | - | 5.0 | 10 | Ohms |
| Transfer Admittance | y _{fs} | V _{DS} =25Vdc, I _D =100mAdc, f=1.0kHz | 50 | - | - | mS |
| DYNAMIC CHARACTERISTICS | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} =5.0Vdc | - | 30 | - | pF |
| Output Capacitance | C _{oss} | V _{DS} =5.0Vdc | - | 10 | - | |
| Transfer Capacitance | C _{rss} | V _{DS} =5.0Vdc | - | 5 | - | |
| SWITCHING CHARACTERISTICS^{NOTE2} | | | | | | |
| Turn-On Delay Time | t _{d(on)} | V _{DD} =-15Vdc, I _D =-2.5Adc, R _L =50Ω | - | 2.5 | - | ns |
| Rise Time | t _r | | - | 1 | - | |
| Turn-Off Delay Time | t _{d(off)} | | - | 16 | - | |
| Fall Time | t _f | | - | 8 | - | |
| Gate Charge | Q _T | | - | 6000 | - | pC |
| SOURCE-DRAIN DIODE CHARACTERISTICS | | | | | | |
| Continuous Current | I _S | | - | - | 0.13 | A |
| Pulsed Current | I _{SM} | | - | - | 0.52 | A |
| Forward Voltage ^{NOTE2} | V _{SD} | | - | 2.5 | - | V |

NOTE1: Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0%.

NOTE2: Switching characteristics are independent of operating junction temperature.



TYPICAL CHARACTERISTICS

$T_A = 25^\circ\text{C}$

Figure 1. Transfer Characteristics

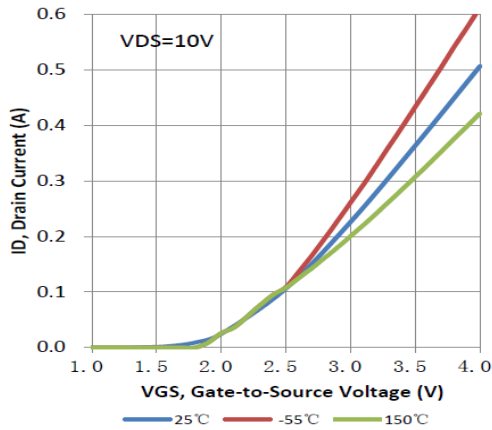


Figure 2. On-Region Characteristics

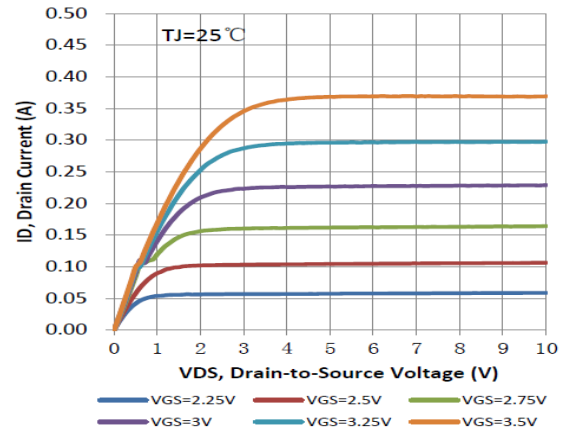


Figure 3. On-Resistance vs. Drain Current

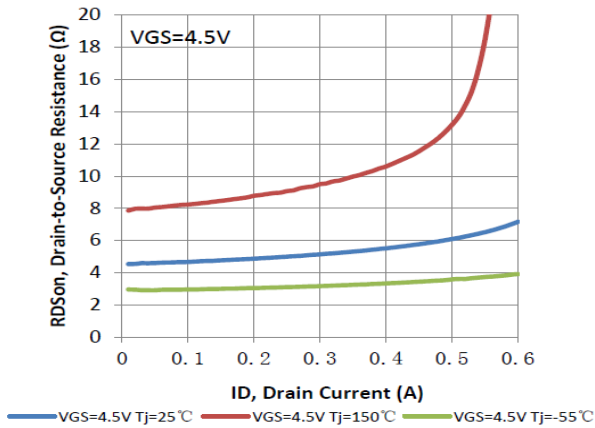


Figure 4. On-Resistance vs. Drain Current

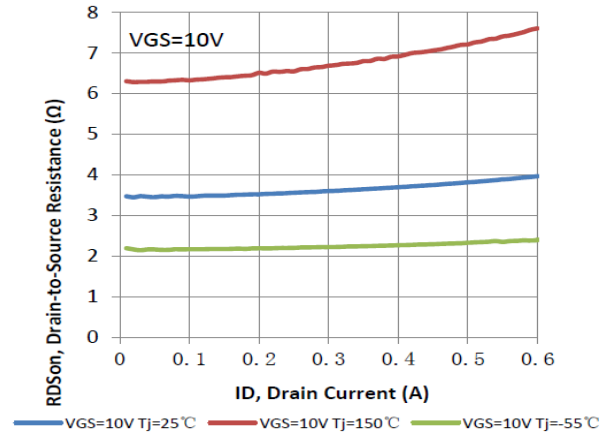


Figure 5. On-Resistance Variation with Temperature

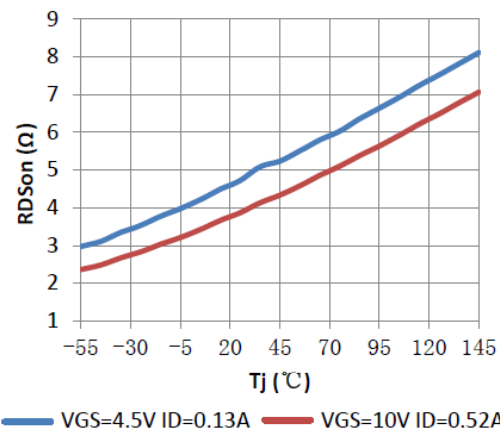
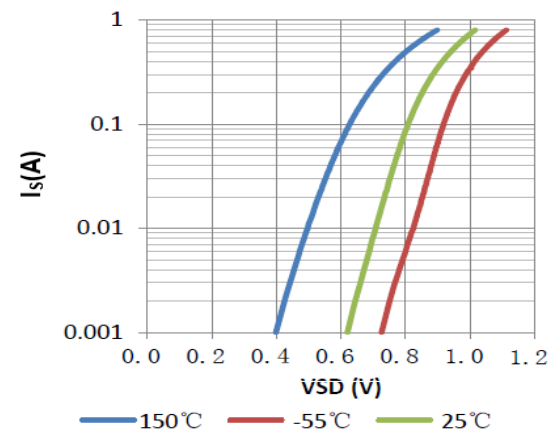


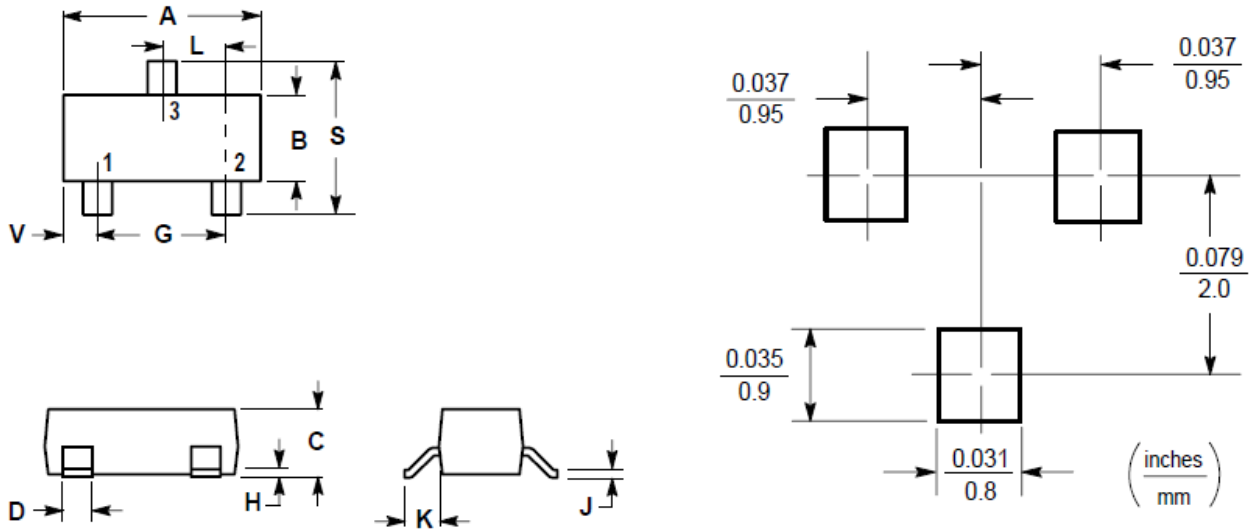
Figure 6. Body Diode Forward Voltage





PACKAGE INFORMATION

Dimension in SOT-23 Package (Unit: mm)



| DIM | INCHES | | MILLIMETERS | |
|-----|--------|--------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.1102 | 0.1197 | 2.80 | 3.04 |
| B | 0.0472 | 0.0551 | 1.20 | 1.40 |
| C | 0.0350 | 0.0440 | 0.89 | 1.11 |
| D | 0.0150 | 0.0200 | 0.37 | 0.50 |
| G | 0.0701 | 0.0807 | 1.78 | 2.04 |
| H | 0.0005 | 0.0040 | 0.013 | 0.100 |
| J | 0.0034 | 0.0070 | 0.085 | 0.177 |
| K | 0.0140 | 0.0285 | 0.35 | 0.69 |
| L | 0.0350 | 0.0401 | 0.89 | 1.02 |
| S | 0.0830 | 0.1039 | 2.10 | 2.64 |
| V | 0.0177 | 0.0236 | 0.45 | 0.60 |



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